

**Status of the claims**

Claims 1-12. Canceled

- 5           Claim 13 (previously amended). A heterojunction bipolar transistor, comprising:  
            a collector region;  
            a SiGe base region;  
            an emitter stack overlaying said collector region, said emitter stack  
including an emitter opening filled with T-shaped polysilicon, said T-shaped polysilicon  
10   overlaying nitride regions included in said stack, and said emitter stack including an  
implant-masking cap layer on top of said T-shaped polysilicon, and wherein said emitter  
stack does not have spacers; and  
            one and another extrinsic base regions arranged on respective sides of said  
emitter stack, said extrinsic base regions being directly aligned with said emitter  
15   polysilicon region but not being directly aligned with said emitter opening.

            Claim 14 (original). The transistor of claim 13, wherein said extrinsic base  
regions are made from SiGe polysilicon.

- 20           Claim 15 (previously amended). The transistor of claim 13, wherein said one of  
said extrinsic base regions is longer than said another of said extrinsic base regions, and  
wherein a base contact is formed on the longer extrinsic base region.

- Claim 16 (previously amended). The transistor of claim 13, wherein said  
25   collector region, emitter stack, and extrinsic base regions are contacted using mid-end-of-  
line collector, emitter, and base contacts respectively.